

300mW, NPN Small Signal Transistor

FEATURES

- Low power loss, high efficiency
- Ideal for automated placement
- High surge current capability
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- Lighting application
- On-board DC/DC converter

MECHANICAL DATA

- Case: SOT-23
- Molding compound: UL flammability classification rating 94V-0
- Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1A whisker test
- · Polarity: Indicated by cathode band
- Weight: 8 mg (approximately)

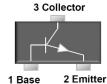
KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
V _{CBO}	75	V	
V_{CEO}	40	V	
V_{EBO}	6	V	
I _C	600	mA	
h _{FE}	300		
Package	SOT-23		
Configuration	Single die		





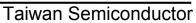






ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)			
PARAMETER	SYMBOL	MMBT2222A	UNIT
Marking code on the device		1P	
Collector-base voltage, emitter open	V _{CBO}	75	V
Collector-emitter voltage, base open	V _{CEO}	40	V
Emitter-base voltage, collector open	V _{EBO}	6	V
Collector current, dc	I _C	600	mA
Total dc power input to all terminals	P _T	300	mW
Junction temperature	TJ	-55 to +150	°C
Storage temperature	T _{STG}	-55 to +150	°C

1





ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage, emitter open	I _C = 10 μA, I _E = 0	$V_{(BR)CBO}$	75	-	-	V
Collector-emitter breakdown voltage, base open	I _C = 10 mA, I _B = 0	V _{(BR)CEO}	40	-	-	V
Emitter-base breakdown voltage, collector open	I _E = 10 μA, I _C = 0	V _{(BR)EBO}	6	-	-	V
Collector cutoff current, emitter open	V _{CB} = 60 V, I _E = 0	I _{CBO}	-	-	0.01	μΑ
Emitter cutoff current, collector open	V _{EB} = 3 V, I _C = 0	I _{EBO}	-	-	0.1	μΑ
	V_{CE} = 10 V, I_{C} = 500 mA		40	-	-	
	V _{CE} = 10 V, I _C = 150 mA		100	-	300	
DC Current Gain	V _{CE} = 10 V, I _C = 10 mA	h _{FE}	75	-	-	
	V _{CE} = 10 V, I _C = 1 mA		50	-	-	
	V _{CE} = 10 V, I _C = 0.1 mA		35	-	-	
Collector-emitter saturation voltage	I _C = 500 mA, I _B = 50 mA	$V_{CE(sat)}$	-	-	1	V
Base-emitter saturation voltage	I _C = 500 mA, I _B = 50 mA	V _{BE(sat)}	-	-	2	V
Transition frequency	$V_{CE} = 20 \text{ V}$, $I_{C} = 20 \text{ mA}$, $I_{C} = 100 \text{ mHz}$	f _T	300	-	-	MHz
Output Capacitance	1 MHz, $V_{CB} = 10 \text{ V}$, $I_{E} = 0$	C _{OBO}	8		pF	
Input Capacitance	1 MHz, V _{EB} = 0.5 V, I _C = 0	C _{IBO}	25		pF	
Delay Time	V_{CC} =30V, $V_{BE(off)}$ = -0.5V, I_{C} =150mA	t _d	-	-	10	ns
Rise Time	I _{B1} =15mA	t _r	-	-	25	ns
Storage Time	V_{CC} =30V, I_{B1} = - I_{B2} =15mA, I_{C} =150mA	t _s	-	-	225	ns
Fall Time	V _{CC} =30V, I _{B1} = -I _{B2} =15mA, I _C =150mA	t _f	-	-	60	ns

ORDERING INFORMATION			
ORDERING CODE	PACKAGE	PACKING	
MMBT2222A RFG	SOT-23	3K / 7" Reel	



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig. 1Max Power Dissipation VS. Ambient Temperature

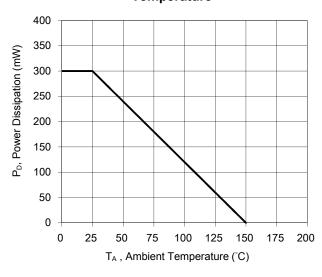


Fig.2 Typical Capacitance

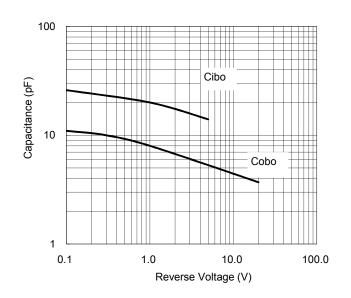


Fig.3 Typical DC Current Gain
VS. Collector Current

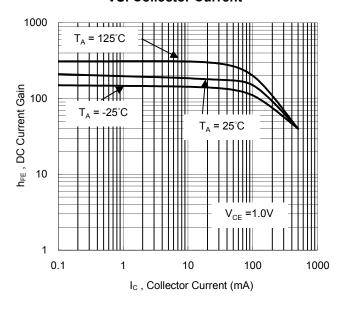
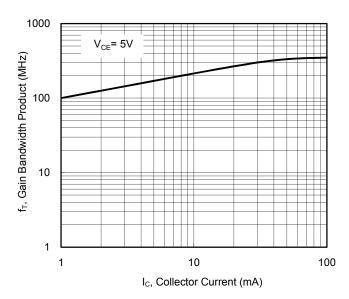


Fig.4 Gain Bandwidth Product VS. Collector Current







CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.5 Collector Emitter Saturation Voltage

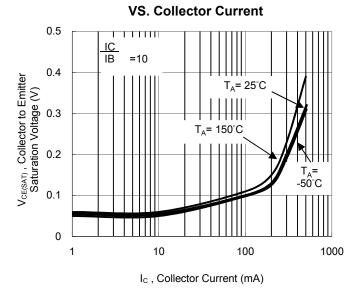
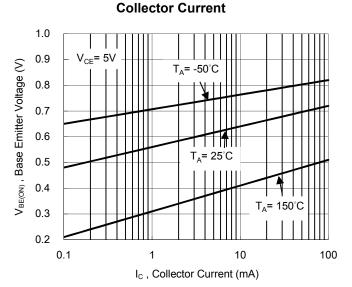


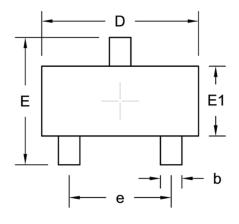
Fig.6 Base Emitter Voltage vs.

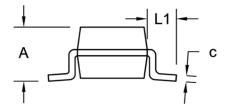




PACKAGE OUTLINE DIMENSION

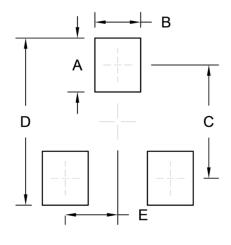
SOT-23





DIM.	Unit (mm)		Unit (inch)	
Dilvi.	Min.	Max.	Min.	Max.
Α	0.89	1.12	0.035	0.044
b	0.30	0.50	0.012	0.020
С	0.08	0.20	0.003	0.008
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E1	1.20	1.40	0.047	0.055
е	1.90 BSC		0.07	5 BSC
L1	0.54 REF.		0.021	I REF.

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	1.00	0.039
В	0.85	0.033
С	2.10	0.083
D	3.10	0.122
E	0.98	0.039



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